



Smart Highside Power Switch

Reversave™

 Reverse battery protection by self turn on of power MOSFET

Features

- Short circuit protection
- Current limitation
- Overload protection
- Thermal shutdown
- Overvoltage protection (including load dump)
- Loss of ground protection
- Loss of V_{bb} protection (with external diode for charged inductive loads)
- Very low standby current
- Fast demagnetisation of inductive loads
- Electrostatic discharge (ESD) protection
- Optimized static electromagnetic compatibility (EMC)
- Green product (RoHS compliant)
- AEC qualified

Diagnostic Function

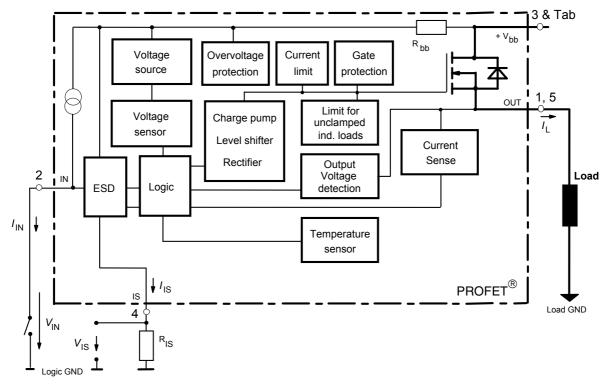
• Proportional load current sense (with defined fault signal during thermal shutdown)

Application

- Power switch with current sense diagnostic feedback for 12V and 24 V DC grounded loads
- All types of resistive, capacitive and inductive loads (no PWM with inductive loads)
- Replaces electromechanical relays, fuses and discrete circuits

General Description

N channel vertical power FET with charge pump, current controlled input and diagnostic feedback with load current sense, integrated in Smart SIPMOS[®] chip on chip technology. Providing embedded protective functions.



Product Summary			
Operating voltage	$V_{ m bb(on)}$	5.036	V
On-state resistance	Ron	16	$\text{m}\Omega$
Load current (ISO)	<i>I</i> L(ISO)	25	Α
Current limitation	<i>I</i> L(SCr)	65	Α

Package

PG-TO252-5-11





Pin	Symbol		Function
1	OUT	0	Output to the load. The pin 1 and 5 must be shorted with each
			other especially in high current applications!*)
2	IN	Ι	Input, activates the power switch in case of short to ground
Tab/(3)	Vbb	+	Positive power supply voltage, the tab is shorted to this pin.
4	IS	S	Diagnostic feedback providing a sense current proportional to the load current; high current on failure (see Truth Table on page 6)
5	OUT	0	Output to the load. The pin 1 and 5 must be shorted with each
			other especially in high current applications!*)

*) Not shorting all outputs will considerably increase the on-state resistance, reduce the peak current capability and decrease the current sense accuracy

Maximum Ratings	at $T_j = 25 ^{\circ}C$ unless	otherwise specified
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Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 4)	V _{bb}	36	V
Supply voltage for full short circuit protection	V _{bb}	24 ¹⁾	V
(see also diagram on page 9) T_{j} =-40150 °C:			
Load dump protection $V_{\text{LoadDump}} = U_{\text{A}} + V_{\text{s}}$, $U_{\text{A}} = 13.5 \text{ V}$ $R_{\text{I}} = 2 \Omega$, $R_{\text{L}} = 2.7 \Omega$, $t_{\text{d}} = 200 \text{ ms}$, IN= low or high	$V_{\rm Load\ dump}^{2)}$	60	V
Load current (Short-circuit current, see page 4)	IL .	self-limited	Α
Operating temperature range	Tj	-40+150	°C
Storage temperature range	T _{stg}	-55+150	
Power dissipation (DC) TC \leq 25°C	P _{tot}	42	W
Inductive load switch-off energy dissipation, single pulse U=12V, I=10A, L=3mH T_{j} =150 °C:	E _{AS}	0.15	J
Electrostatic discharge capability (ESD) (Human Body Model) acc. ESD assn. std. S5.1-1993; R=1.5kΩ; C=100pF	V _{ESD}	4.0	kV
Current through input pin (DC)	I _{IN}	+15, -100	mA
Current through current sense pin (DC)	I _{IS}	+15, -100	
see internal circuit diagrams page 7			

¹⁾ Short circuit is tested with 100m Ω and 20 μH

²⁾ $V_{\text{Load dump}}$ is set-up without the DUT connected to the generator per ISO 7637-1 and DIN 40839



Thermal Characteristics

Parameter and Conditions		Symbol	Values			Unit
		_	min	typ	max	
Thermal resistance	chip - case:	$R_{\rm thJC}^{3)}$			1.5	K/W
junc	tion - ambient (free air):	$R_{ m thJA}$		80		
SMD ve	ersion, device on PCB ⁴⁾ :			45		

Electrical Characteristics

Parameter and Conditions	Symbol	Values			Unit
at T_{j} = -40°C150°C, V_{bb} = 12 V unless otherwise specified		min	typ	max	

Load Switching Capabilities and Characteristics

On-state resistance (pin 3 to pin 1,5)					
$V_{\rm IN}=0, \ I_{\rm L}=5 \ {\rm A}$ $T_{\rm j}=25 \ {\rm °C}:$	R _{ON}		13	16	mΩ
<i>T</i> j=150 °C:			25	31	
Output voltage drop limitation at small load currents (Tab to pin 1,5) T_{j} =-40150 °C:	V _{ON(NL)}		50		mV
Nominal load current (Tab to pin 1,5)					Α
ISO Proposal: <i>T</i> _C =85°C, <i>V</i> _{ON} ≤0.5V, <i>T</i> _j ≤150°C	I _{L(ISO)}	21	25		
SMD ⁴): <i>T</i> _A =85°C, <i>V</i> _{ON} ≤0.5V, <i>T</i> _j ≤150°C	I _{L(nom)}	6.2	7.6		
Turn-on time I_{IN} to 90% V_{OUT} :	<i>t</i> on	150		410	μs
Turn-off time $I_{IN} \perp$ to 10% V_{OUT} :	<i>t</i> off	70		410	
<i>R</i> _L = 2,5Ω, <i>T</i> _j =-40150 °C					
Slew rate on	dV/dt _{on}	0.1		1	V/µs
10 to 30% <i>V</i> _{OUT} , <i>R</i> _L = 2.5 Ω, <i>T</i> _j =-40150 °C					
Slew rate off 70 to 40% V_{OUT} , $R_{L} = 2.5 \Omega$, T_{j} =-40150 °C	-d <i>V</i> /dt _{off}	0.1		1	V/µs

³⁾ Thermal resistance R_{thCH} case to heatsink (about 0.5 ... 0.9 K/W with silicone paste) not included!

⁴⁾ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70µm thick) copper area for V_{bb} connection. PCB is vertical without blown air.



Parameter and Conditions	Symbol	Values			Unit
at T_{j} = -40°C150°C, V_{bb} = 12 V unless otherwise specified		min	typ	max	

Operating Parameters

Operating voltage (V _{IN} =0V)		V _{bb(on)}	5.0		36	V
Undervoltage shutdown ⁵⁾		V _{bIN(u)}	1.5	3.0	4.5	V
Undervoltage restart of charg	e pump (V _{IN} =0V)	V _{bb(ucp)}	3.0	4.5	6.0	V
Overvoltage protection ⁶⁾ <i>I</i> _{bb} =15 mA		V _{Z,IN}	61	68		V
Standby current	<i>T</i> _j =-40+25°C:	I _{bb(off)}		2	5	μA
/ _{IN} =0	<i>T</i> j=150°C:			4	8	

Protection Functions 7)

Short circuit current limit (Tab to pin 1,5)					
V_{ON} =8V, time until limitation max. 300 μ s					
<i>T</i> _j =-40°C: <i>T</i> _j =25°C: <i>T</i> _j =+150°C:	I _{L(SC)}	35 35 35	75 65 65	110 110 125	A
Repetitive short circuit current limit, $T_j = T_{jt}$	I _{L(SCr)}		65		Α
Output clamp (inductive load switch off) at $V_{OUT} = V_{bb}$ - $V_{ON(CL)}$ (e.g. overvoltage) I_L = 40 mA ⁸	V _{ON(CL)}	38	42	48	V
Thermal overload trip temperature	T _{jt}	150			°C
Thermal hysteresis	ΔT_{jt}		10		K

Reverse Battery

Reverse battery voltage	-V _{bb}	 	20	V
On-state resistance (pin 1,5 to pin 3)				
$V_{\rm bb}$ = -8V, $V_{\rm IN}$ = 0, $I_{\rm L}$ = -5 A, $R_{\rm IS}$ = 1 k Ω , $T_{\rm j}$ =25 °C:	R _{ON(rev)}	 	22	mΩ
$V_{\rm bb}$ = -12V, $V_{\rm IN}$ = 0, $I_{\rm L}$ = -5 A, $R_{\rm IS}$ = 1 k Ω , $T_{\rm j}$ =25 °C:		 16	19	
<i>T</i> j=150 °C:		25	32	
Integrated resistor in V_{bb} line	R _{bb}	 200		Ω

⁵⁾ VbIN=Vbb-VIN see diagram on page 11.

⁶⁾ see also $V_{ON(CL)}$ in circuit diagram on page 7.

⁷⁾ Integrated protection functions are designed to prevent IC destruction under fault condition described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not for continuous repetitive operation.

⁸⁾ see also page 12.



Diagnostic Characteristics

Current sense ratio, static on-condition	<i>k</i> _{ILIS}		8200		
$k_{ILIS} = I_L : I_{IS}$ $V_{ON} < 1.5 \text{ V}, V_{IS} < V_{OUT} - 5 \text{ V}, V_{\text{bIN}} > 4.5 \text{ V}^{9)}$					
IL = 20A, Tj = -40°C Tj = +25°C Tj = +150°C		7400 7500 7500	8300 8300 8200	9100 9100 8800	
IL = 5A, Tj = -40°C Tj = +25°C Tj = +150°C		6800 7200 7200	8300 8300 8200	9700 9300 9000	
IL = 2.5A, Tj = -40°C Tj = +25°C Tj = +150°C		6800 6800 6800	8500 8500 8100	10000 9800 9200	
IL = 1A, Tj = -40°C Tj = +25°C Tj = +150°C		6800 6800 6800	8600 8600 8600	10500 10500 10500	
$I_{\rm IN} = 0$ (e.g. during de-energising of inductive loads)			n.a.		
Sense current under fault conditions;					
$V_{\rm DS}$ >1.5V, typ. $T_{\rm j}$ = -40+150°C	I _{IS,fault}	2.5	4		mA
Fault-Sense signal delay after negative input slope	tdelay(fault)			0.8	ms
Current sense leakage current					
$l_{\rm IN} =$	D: I _{IS(LL)}			0.5	μA
$V_{IN} = 0, I_{L} =$			4	12	
Current sense settling time to $I_{IS \text{ static}} \pm 10\%$ after positive input slope, $I_L = 0 \int 20 \text{ A}^{-10}$ $T_{i} = -40+150^{\circ}$	t _{son(IS)}			400	μs
Overvoltage protection					
$I_{bb} = 15 \text{ mA}$ $T_j = -40+150^{\circ}\text{C}$	$V_{\rm bIS(Z)}$	61	68		V
Input					

Required current capability of input switch $T_j = -40+150^{\circ}C$:	I _{IN(on)}	 0.7	1.2	mA
Maximum input current for turn-off $T_j = -40+150^{\circ}C$:	I _{IN(off)}	 	50	μA

⁹⁾ If V_{ON} is higher, the sense current is no longer proportional to the load current due to sense current saturation.

¹⁰) Not subject to production test, specified by design.

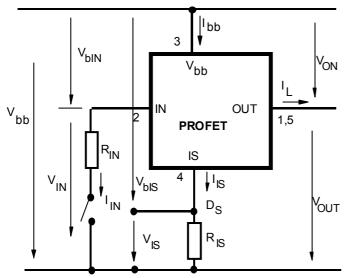


Truth Table

	Input	Output	Current
	Current		Sense
	level	level	lis
Normal	L	L	0
operation	н	н	nominal
Overload	L	L	0
	н	н	I _{ISfault}
Short circuit to GND	L	L	0
	н	L	I _{ISfault}
Overtemperature	L	L	0
	н	L	I _{ISfault}
Short circuit to Vbb	L	Н	0
	н	Н	<nominal<sup>11</nominal<sup>
Open load	L	Z	0
	Н	Н	0

L = "Low" Level H = "High" Level Z = high impedance, potential depends on external circuit

Terms

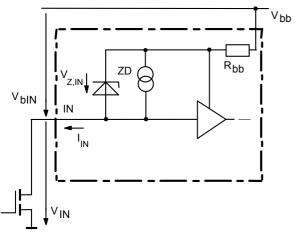


Two or more devices can easily be connected in parallel to increase load current capability.

¹¹⁾ Low ohmic short to $V_{\rm bb}$ may reduce the output current $I_{\rm L}$ and therefore also the sense current $I_{\rm IS}$.



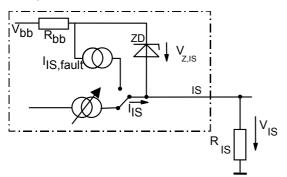
Input circuit (ESD protection)



ESD-Zener diode: 68 V typ., max 15 mA;

Current sense output

Normal operation



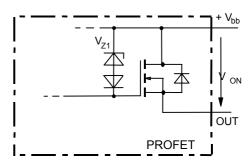
 $V_{Z,IS} = 68 V$ (typ.), $R_{IS} = 1 k\Omega$ nominal (or $1 k\Omega / n$, if n devices are connected in parallel). $I_S = I_L / k_{ilis}$ can be only driven by the internal circuit as long as

 $V_{\text{out}} - V_{\text{IS}} > 5V$. If you want to measure load currents up to h as Bio should be less than $\frac{V_{bb} - 5V}{V_{bb}}$

up to $I_{L(M)}$, R_{IS} should be less than $\frac{V_{bb}}{I_{L(M)}} / K_{ilis}$

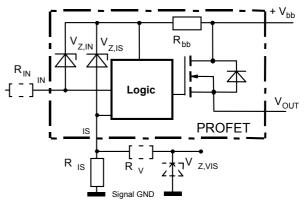
Note: For large values of R_{IS} the voltage V_{IS} can reach almost V_{bb}. See also overvoltage protection. If you don't use the current sense output in your application, you can leave it open.

Inductive and overvoltage output clamp



 V_{ON} is clamped to $V_{ON(CI)} = 42 V$ typ.

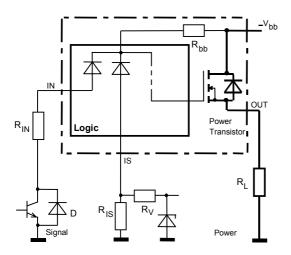
Overvoltage protection of logic part



$$\begin{split} R_{bb} = &200\,\Omega\,typ., \ V_{Z,IN} = V_{Z,IS} = &68\,V\,typ., \ R_{IS} = &1\,k\Omega\\ nominal. \ Note that when overvoltage exceeds 73\,V\,typ.\\ a voltage above 5V can occur between IS and GND, if R_V, V_{Z,VIS} are not used. \end{split}$$



Reversave[™] (Reverse battery protection)



 $R_{V} \ge 1 k\Omega$, $R_{IS} = 1 k\Omega$ nominal. Add R_{IN} for reverse battery protection in applications with V_{bb} above 16V;

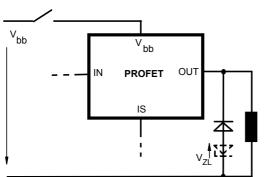
recommended value: $\frac{1}{R_{\text{IN}}} + \frac{1}{R_{\text{IS}}} + \frac{1}{R_{\text{V}}} = \frac{0.05A}{|V_{bb}| - 12V}$

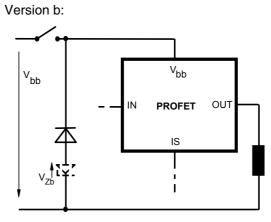
To minimise power dissipation at reverse battery operation, the summarised current into the IN and IS pin should be about 50mA. The current can be provided by using a small signal diode D in parallel to the input switch, by using a MOSFET input switch or by proper adjusting the current through R_{IS} and R_{V} . Since the current through R_{bb} generates additional heat in the device, this has to be taken into account in the overall thermal considerations.

V_{bb} disconnect with energised inductive load

Provide a current path with load current capability by using a diode, a Z-diode, or a varistor. ($V_{ZL} < 73$ V or $V_{Zb} < 30$ V if R_{IN}=0). For higher clamp voltages currents at IN and IS have to be limited to 250 mA.

Version a:

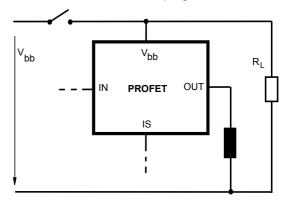




Note that there is no reverse battery protection when using a diode without additional Z-diode V_{ZL} , V_{Zb} .

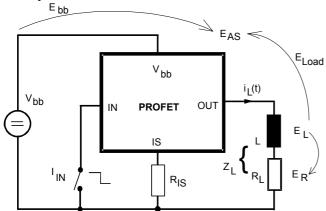
Version c:

Sometimes a necessary voltage clamp is given by non inductive loads R_L connected to the same switch and eliminates the need of clamping circuit:





Inductive load switch-off energy dissipation



Energy stored in load inductance:

$$E_{\rm L} = \frac{1}{2} \cdot {\rm L} \cdot {\rm I}_{\rm L}^2$$

While demagnetising load inductance, the energy dissipated in PROFET is

$$E_{AS} = E_{bb} + E_L - E_R = \int V_{ON(CL)} \cdot i_L(t) dt,$$

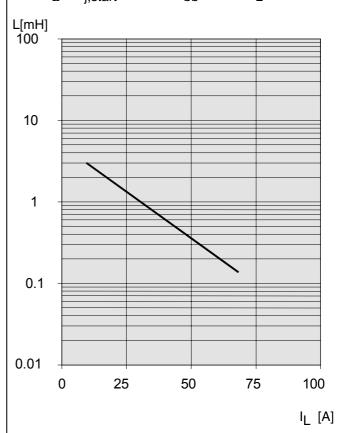
with an approximate solution for $R_L > 0 \Omega$:

$$E_{AS} = \frac{I_{L} \cdot L}{2 \cdot R_{L}} \left(V_{bb} + |V_{OUT(CL)}| \right) ln \left(1 + \frac{I_{L} \cdot R_{L}}{|V_{OUT(CL)}|} \right)$$

The device is not suitable for permanent PWM with inductive loads if active clamping occurs every cycle.

Maximum allowable load inductance for a single switch off

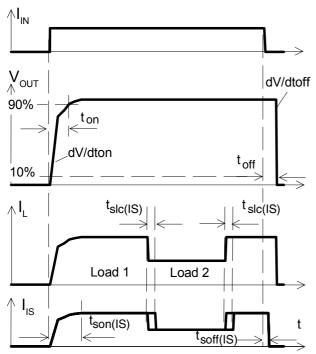
 $L = f(I_L)$; T_{i,start} = 150°C, V_{bb} = 12 V, R_L = 0 Ω





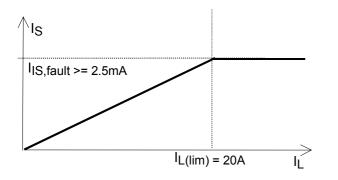
Timing diagrams

Figure 1a: Switching a resistive load, change of load current in on-condition:



The sense signal is not valid during a settling time after turn-on/off and after change of load current.

Figure 1b: typical behaviour of sense output:



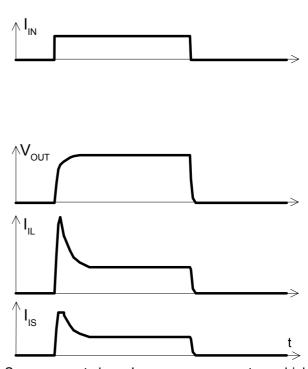
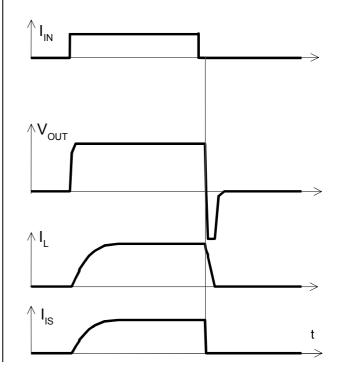


Figure 2a: Switching motors and lamps:

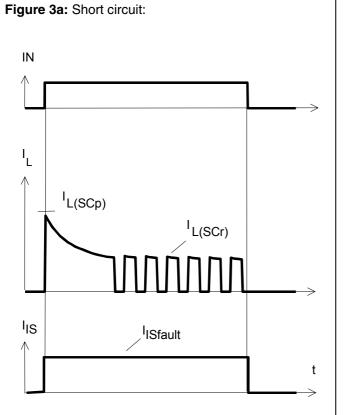
Sense current above I_{IS,fault} can occur at very high inrush currents.

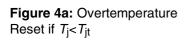
Figure 2b: Switching an inductive load:





PROFET[®] BTS 443 P





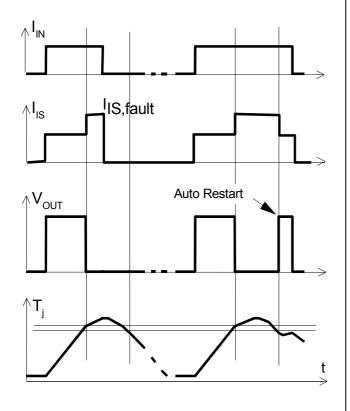
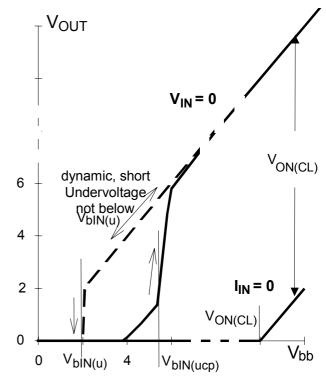
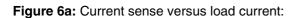


Figure 5a: Undervoltage restart of charge pump, overvoltage clamp





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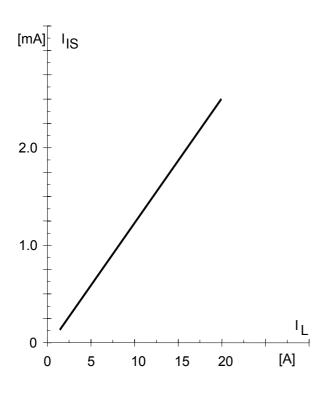
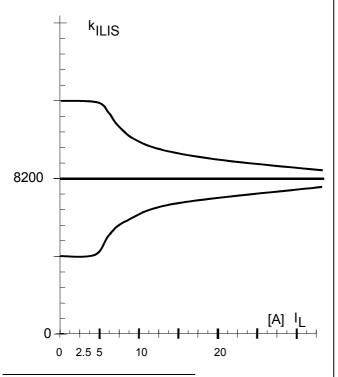
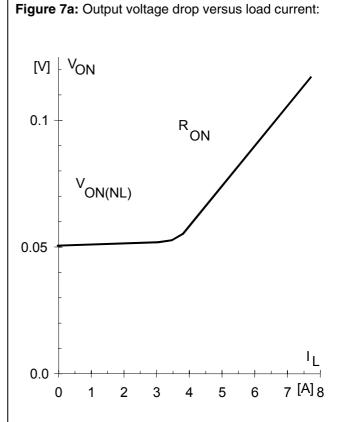


Figure 6b: Current sense ratio¹²:



¹² ⁾ This range for the current sense ratio refers to all devices. The accuracy of the $k_{\rm ILIS}$ can be raised by means of calibration the value of $k_{\rm ILIS}$ for every single device.



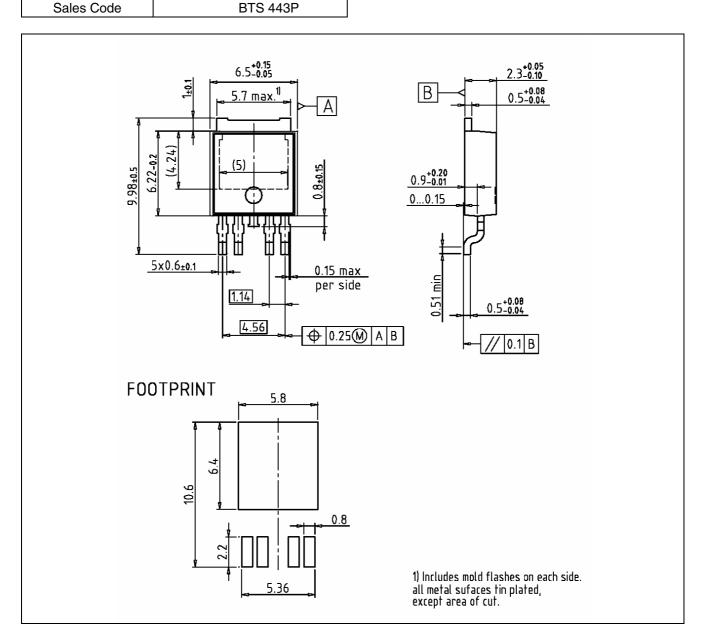


Package Outlines

All dimensions in mm

D-Pak-5 Pin: PG-TO252-5-11

Sales Code



Green Product

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pbfree finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).



Revision History

Version	Date	Changes
Rev. 1.0	2007-02-21	RoHS-compliant version of BTS443P
		Page 1, page 13: RoHS compliance statement and Green product feature added
		Page 1, page 13: Change to RoHS compliant package PG-TO252-5-11
		Legal disclaimer updated

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